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December 2012

# **FDMS2572**

# N-Channel UltraFET Trench<sup>®</sup> MOSFET 150V, 27A, 47mΩ

#### **Features**

- Max  $r_{DS(on)}$  = 47m $\Omega$  at  $V_{GS}$  = 10V,  $I_D$  = 4.5A
- Max  $r_{DS(on)}$  = 53m $\Omega$  at  $V_{GS}$  = 6V,  $I_D$  = 4.5A
- Low Miller Charge
- Optimized efficiency at high frequencies
- UIS Capability (Single pulse and Repetitive pulse)
- RoHS Compliant

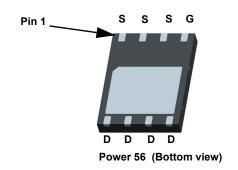


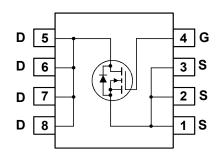
# **General Description**

UltraFET devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for  $r_{DS(on)}$ , low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

# **Application**

- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier





# **MOSFET Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

| Symbol                            | Parameter                                    |                       |           | Ratings     | Units |
|-----------------------------------|----------------------------------------------|-----------------------|-----------|-------------|-------|
| $V_{DS}$                          | Drain to Source Voltage                      |                       |           | 150         | V     |
| $V_{GS}$                          | Gate to Source Voltage                       |                       |           | ±20         | V     |
|                                   | Drain Current -Continuous (Package limited)  | T <sub>C</sub> = 25°C |           | 27          |       |
|                                   | -Continuous (Silicon limited)                | T <sub>C</sub> = 25°C |           | 27          | Α     |
| I <sub>D</sub>                    | -Continuous                                  | T <sub>A</sub> = 25°C | (Note 1a) | 4.5         |       |
|                                   | -Pulsed                                      |                       |           | 30          |       |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy                |                       | (Note 3)  | 150         | mJ    |
| В                                 | Power Dissipation                            | T <sub>C</sub> = 25°C |           | 78          | W     |
| $P_{D}$                           | Power Dissipation                            | T <sub>A</sub> = 25°C | (Note 1a) | 2.5         | VV    |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature R | ange                  |           | -55 to +150 | °C    |

## **Thermal Characteristics**

| $R_{\theta JC}$ | Thermal Resistance, Junction to Case    |           | 1.6 | °C/W |
|-----------------|-----------------------------------------|-----------|-----|------|
| $R_{\theta,IA}$ | Thermal Resistance, Junction to Ambient | (Note 1a) | 50  | C/VV |

# **Package Marking and Ordering Information**

| Device Marking | Device   | Package  | ackage Reel Size Tape Width |  | Quantity   |
|----------------|----------|----------|-----------------------------|--|------------|
| FDMS2572       | FDMS2572 | Power 56 | 13" 12mm 3000               |  | 3000 units |

# **Electrical Characteristics** T<sub>J</sub> = 25°C unless otherwise noted

| Symbol                               | Parameter                                 | Test Conditions                              | Min | Тур | Max  | Units |
|--------------------------------------|-------------------------------------------|----------------------------------------------|-----|-----|------|-------|
| Off Chara                            | octeristics                               |                                              |     |     |      |       |
| BV <sub>DSS</sub>                    | Drain to Source Breakdown Voltage         | $I_D = 250 \mu A, V_{GS} = 0 V$              | 150 |     |      | V     |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | I <sub>D</sub> = 250μA, referenced to 25°C   |     | 180 |      | mV/°C |
| I <sub>DSS</sub>                     | Zero Gate Voltage Drain Current           | V <sub>DS</sub> = 120V, V <sub>GS</sub> = 0V |     |     | 1    | μΑ    |
| I <sub>GSS</sub>                     | Gate to Source Leakage Current            | V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V |     |     | ±100 | nA    |

### On Characteristics (Note 2)

| V <sub>GS(th)</sub>                    | Gate to Source Threshold Voltage                            | $V_{GS} = V_{DS}, I_{D} = 250 \mu A$           | 2 | 3    | 4   | V     |
|----------------------------------------|-------------------------------------------------------------|------------------------------------------------|---|------|-----|-------|
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage<br>Temperature Coefficient | I <sub>D</sub> = 250μA, referenced to 25°C     |   | -9.8 |     | mV/°C |
|                                        |                                                             | $V_{GS} = 10V, I_D = 4.5A$                     |   | 36   | 47  |       |
| r <sub>DS(on)</sub> Drain              | Drain to Source On Resistance                               | $V_{GS} = 6V$ , $I_{D} = 4.5A$                 |   | 39   | 53  | mΩ    |
|                                        |                                                             | $V_{GS} = 10V$ , $I_D = 4.5A$ , $T_J = 125$ °C |   | 69   | 103 |       |
| 9 <sub>FS</sub>                        | Forward Transconductance                                    | $V_{DS} = 10V, I_D = 4.5A$                     |   | 14   |     | S     |

# **Dynamic Characteristics**

| C <sub>iss</sub> | Input Capacitance            | 75)/ )/                                                    |     | 1960 | 2610 | pF |
|------------------|------------------------------|------------------------------------------------------------|-----|------|------|----|
| C <sub>oss</sub> | Output Capacitance           | V <sub>DS</sub> = 75V, V <sub>GS</sub> = 0V,<br>— f = 1MHz |     | 130  | 175  | pF |
| C <sub>rss</sub> | Reverse Transfer Capacitance | 1 - 1101112                                                |     | 30   | 45   | pF |
| $R_g$            | Gate Resistance              | f = 1MHz                                                   | 0.1 | 1.3  | 2.6  | Ω  |

# **Switching Characteristics**

| t <sub>d(on)</sub>  | Turn-On Delay Time            |                                              |  | 11 | 20 | ns |
|---------------------|-------------------------------|----------------------------------------------|--|----|----|----|
| t <sub>r</sub>      | Rise Time                     | $V_{DD} = 75V, I_D = 1.0A$                   |  | 8  | 16 | ns |
| t <sub>d(off)</sub> | Turn-Off Delay Time           | $V_{GS} = 10V$ , $R_{GEN} = 6\Omega$         |  | 38 | 61 | ns |
| t <sub>f</sub>      | Fall Time                     |                                              |  | 31 | 50 | ns |
| $Q_{g(TOT)}$        | Total Gate Charge at 10V      | $V_{GS} = 0V \text{ to } 10V$ $V_{DD} = 75V$ |  | 31 | 43 | nC |
| Q <sub>gs</sub>     | Gate to Source Gate Charge    | I <sub>D</sub> = 4.5A                        |  | 9  |    | nC |
| $Q_{gd}$            | Gate to Drain "Miller" Charge |                                              |  | 7  |    | nC |

### **Drain-Source Diode Characteristics**

| $V_{SD}$        | Source to Drain Diode Forward Voltage | $V_{GS} = 0V, I_S = 2.2A$ (Note 2)     |  | 0.7 | 1.0 | V  |
|-----------------|---------------------------------------|----------------------------------------|--|-----|-----|----|
| t <sub>rr</sub> | Reverse Recovery Time                 | I <sub>F</sub> = 4.5A, di/dt = 100A/μs |  | 67  | 101 | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge               |                                        |  | 130 | 195 | nC |

1:  $R_{\text{QJA}}$  is determined with the device mounted on a 1in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\text{QJC}}$  is guaranteed by design while  $R_{\text{QCA}}$  is determined by the user's board design.



a.50°C/W when mounted on a 1 in² pad of 2 oz copper



b. 125°C/W when mounted on a minimum pad of 2 oz copper

- 2: Pulse Test: Pulse Width < 300 $\mu$ s, Duty cycle < 2.0%. 3: E<sub>AS</sub> of 150 mJ is based on starting T<sub>J</sub> = 25 °C, L = 3 mH, I<sub>AS</sub> = 10 A, VDD = 150 V, VGS = 10 V.

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

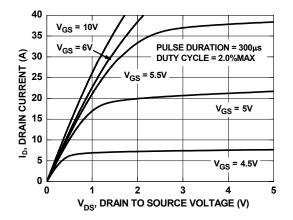


Figure 1. On-Region Characteristics

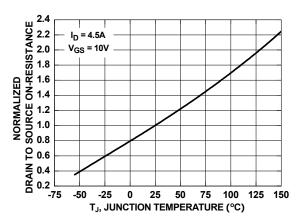


Figure 3. Normalized On - Resistance vs Junction Temperature

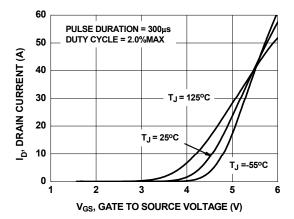


Figure 5. Transfer Characteristics

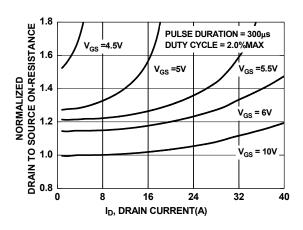


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

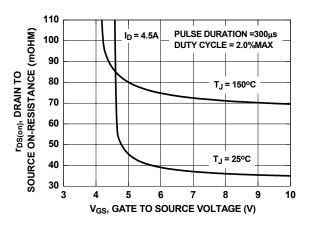


Figure 4. On-Resistance vs Gate to Source Voltage

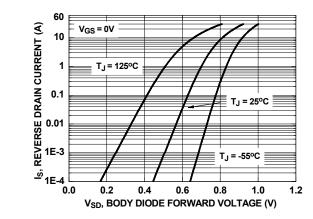


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

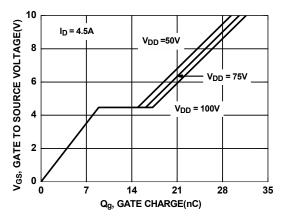


Figure 7. Gate Charge Characteristics

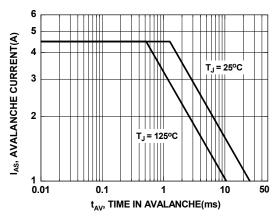


Figure 9. Unclamped Inductive Switching Capability

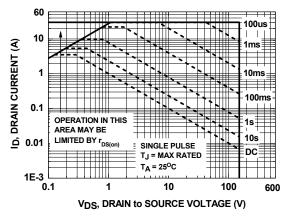


Figure 11. Forward Bias Safe Operating Area

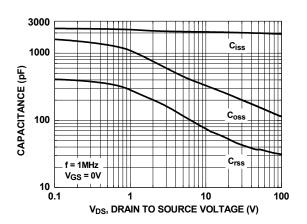


Figure 8. Capacitance vs Drain to Source Voltage

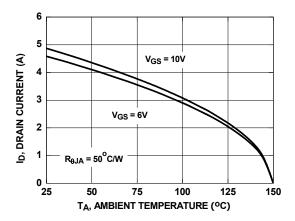


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

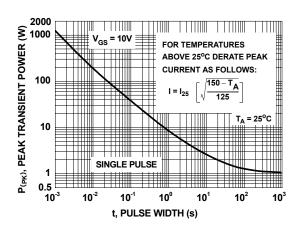


Figure 12. Single Pulse Maximum Power Dissipation

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

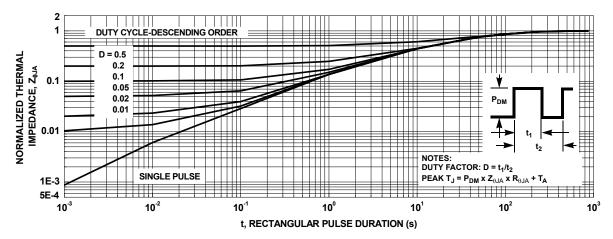
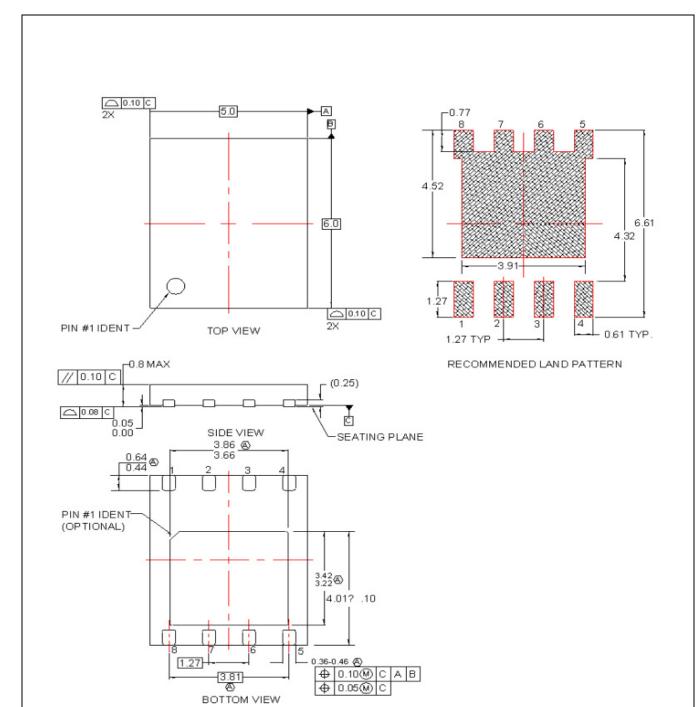


Figure 13. Transient Thermal Response Curve



#### NOTES:

- ODES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229. DATED 11/2001.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
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